



#### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D Max</sub> T <sub>A</sub> = +25°C
-20V	$78m\Omega @ V_{GS} = -8V$	-4.0A
-200	100mΩ @ $V_{GS} = -4.5V$	-3.5A

## **Description**

This new generation MOSFET is designed to minimize the footprint in handheld and Mobile application. It can be used to replace many small signals MOSFET with as really small footprint.

## **Applications**

- Battery Management
- Load Switch
- Battery Protection
- Handheld and Mobile Application

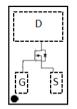
## **Features and Benefits**

- Low Qg & Qgd
- Small Footprint
- Low Profile 0.20mm Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

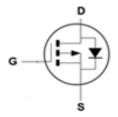
### **Mechanical Data**

- Case: X4-DSN1006-3
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu or NiAu. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.00029 grams (Approximate)

#### X4-DSN1006-3



Top View



**Equivalent Circuit** 

March 2020

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### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2077UCA3-7	X4-DSN1006-3	10k/Tape & Reel
DMP2077UCA3-7A	X4-DSN1006-3	10k/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



Q = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: H = 2020) M or  $\overline{M}$  = Month (ex: 9 = September)

#### Date Code Key

Year	2018		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	F		Н	ı	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-20	V		
Gate-Source Voltage			Vgss	±12	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -8V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	-4.0 -3.2	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-3.5 -2.8	А		
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-16	Α		

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P <sub>D</sub>	0.66	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	Reja	197	°C/W
Power Dissipation (Note 5)	PD	1.98	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	Reja	65	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

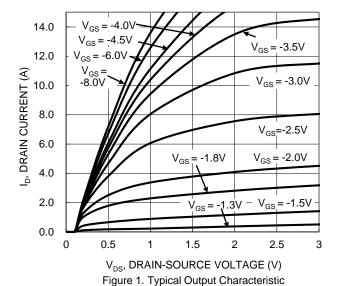
## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	Зуппоп	IVIIII	Тур	IVIAX	Unit	rest condition	
Drain-Source Breakdown Voltage	BVpss	-20	_		V	V <sub>G</sub> S = 0V, I <sub>D</sub> = -250μA	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	_	-100	nA	$V_{DS} = -16V, V_{GS} = 0V$	
Gate-Source Leakage	Igss			±50	nA	$V_{GS} = 10V, V_{GS} = 0V$ $V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	1633			200	117 (	VGS - ±12V, VDS - 0V	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.5	-0.85	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA	
Cate 1111001101a Voltage	V 00(111)		66	78	•	$V_{GS} = -8V$ , $I_{D} = -0.5A$	
			78	100		VGS = -4.5V, ID = -0.5A	
Static Drain-Source On-Resistance	RDS(ON)		112	165	mΩ	VGS = -2.5V, ID = -0.5A	
Otalio Diani Godino Giri (Godina	1100(014)		165	600		$V_{GS} = -1.8V, I_{D} = -0.1A$	
			295	900		VGS = -1.5V, ID = -0.1A	
Diode Forward Voltage	Vsp		-0.73	-1.0	V	$V_{GS} = 0V$ , $I_{S} = -0.5A$	
Reverse Recovery Charge	QRR		1.3	_	nC	$V_{DD} = -10V$ , $I_F = -1A$ ,	
Reverse Recovery Time	trr		7.7	_	ns	$di/dt = 100A/\mu s$	
DYNAMIC CHARACTERISTICS (Note 9)	THE					10.00	
Input Capacitance	Ciss	_	143	_			
Output Capacitance	Coss		76	_	pF	$V_{DS} = -10V$ , $V_{GS} = 0V$ ,	
Reverse Transfer Capacitance	Crss		3.2	_		f = 1MHz	
Series Gate Resistance	Rg		4.7	_	Ω	f = 1MHz, V <sub>G</sub> S = 0V, V <sub>D</sub> S = 0V	
Total Gate Charge	Qg		1.34	_		, ,	
Gate-Source Charge	Qgs		0.12	_		V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V,	
Gate-Drain Charge	Q <sub>qd</sub>		0.15	_	nC	I <sub>D</sub> = -0.5A	
Gate Charge at VTH	Q <sub>g(TH)</sub>	_	0.24	_			
Turn-On Delay Time	t <sub>D</sub> (ON)		15.4	_			
Turn-On Rise Time	t <sub>R</sub>	_	5.7	_		V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V,	
Turn-Off Delay Time	tD(OFF)	_	5.8	_	ns	$R_g = 2\Omega$ , $I_D = -0.5A$	
Turn-Off Fall Time	tr	_	5.4	_			

Notes:

- Device mounted on FR-4 material with 1inch² (6.45cm²), 2oz. (0.071mm thick) Cu.
  Repetitive rating, pulse width limited by junction temperature.
  Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to production testing.





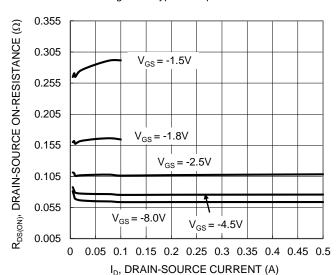


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

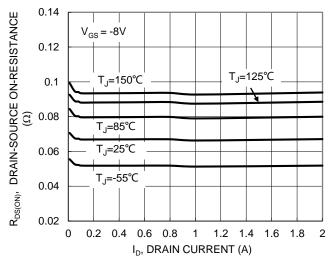
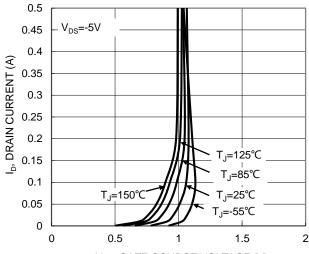


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



 $V_{\text{GS}}$ , GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

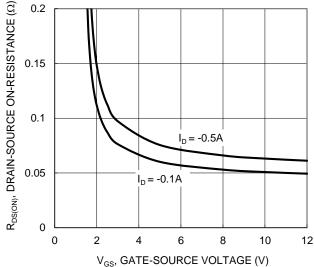


Figure 4. Typical Transfer Characteristic

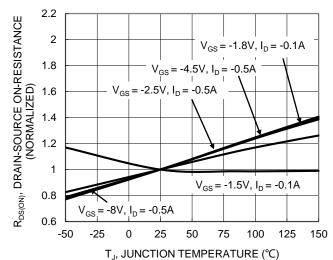


Figure 6. On-Resistance Variation with Junction Temperature



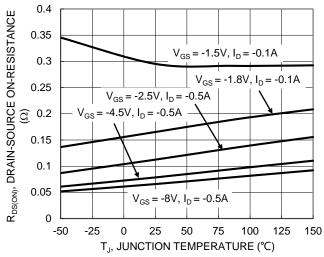


Figure 7. On-Resistance Variation with Junction Temperature

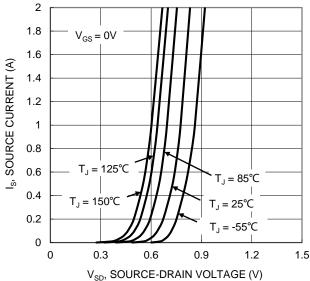


Figure 9. Diode Forward Voltage vs. Current

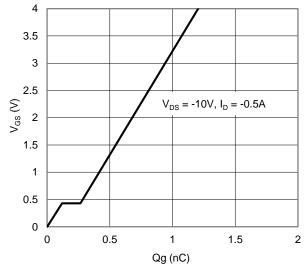


Figure 11. Gate Charge

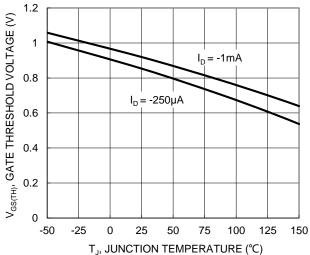


Figure 8. Gate Threshold Variation vs. Junction Temperature

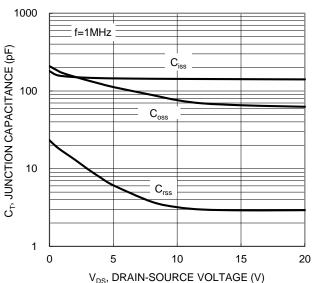


Figure 10. Typical Junction Capacitance

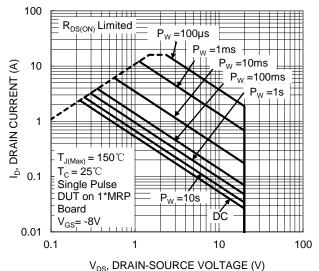


Figure 12. SOA, Safe Operation Area



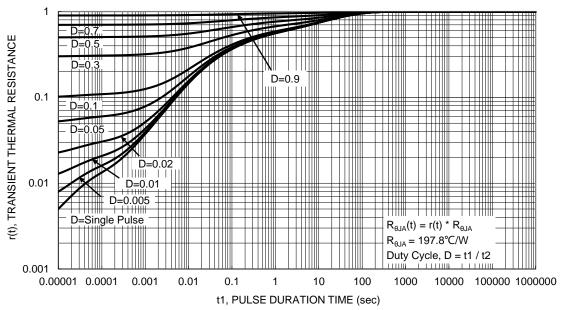


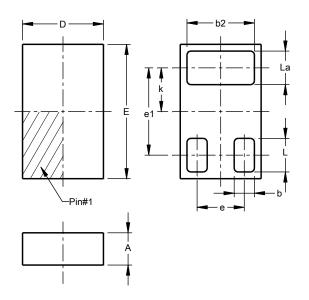
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X4-DSN1006-3

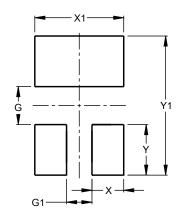


X4-DSN1006-3							
Dim	Min	Max	Тур				
Α	0.18	0.22	0.20				
b	0.14	0.16	0.15				
b2	0.49	0.51	0.50				
D	0.56	0.64	0.60				
Е	0.96	1.04	1.00				
е			0.35				
e1	ŀ	1	0.65				
k			0.325				
L	0.24	0.26	0.25				
La	0.24	0.26	0.25				
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X4-DSN1006-3



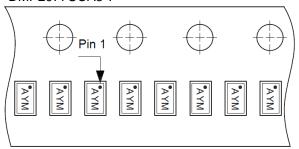
Dimensions	Value (in mm)		
G	0.40		
G1	0.20		
Х	0.15		
X1	0.50		
Y	0.25		
Y1	0.90		



## **Tape and Reel Information**

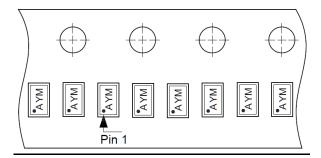
Please see https://www.diodes.com/assets/Packaging-Support-Docs/ap02007.pdf for the latest version.

#### DMP2077UCA3-7



### DMP2077UCA3-7A

Change the PIN1 orientation in the carrier tape, rotate 180 degrees (Top side).





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